

ABSTRACT OF THE DISCLOSURE

A semiconductor device has a substrate and an electrode layer formed on the substrate, and the electrode layer includes a plurality of conductive layers and an
5 insulating layer which are stacked, the insulating layer being interposed between two of the conductive layers adjacent each other, a through-hole being formed in each of the conductive layers lower than an uppermost conductive layer among the conductive layers, and the through-hole being filled with an insulating material.